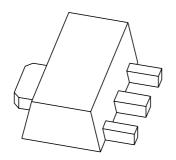
## DISCRETE SEMICONDUCTORS

# DATA SHEET



# PXT4401 NPN switching transistor

Product data sheet Supersedes data of 1999 Apr 14 2004 Nov 22



## **NPN** switching transistor

**PXT4401** 

### **FEATURES**

- High current (max. 600 mA)
- Low voltage (max. 40 V).

### **APPLICATIONS**

 Switching and linear amplification in industrial and consumer applications.

### **DESCRIPTION**

NPN switching transistor in a SOT89 plastic package. PNP complement: PXT4403.

### **MARKING**

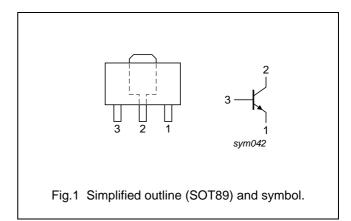
TYPE NUMBER	MARKING CODE(1)			
PXT4401	*2X			

### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

### **PINNING**

PIN	DESCRIPTION
1	emitter
2	collector
3	base



### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE					
TIFE NOMBER	NAME	DESCRIPTION	VERSION				
PXT4401	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89				

### NPN switching transistor

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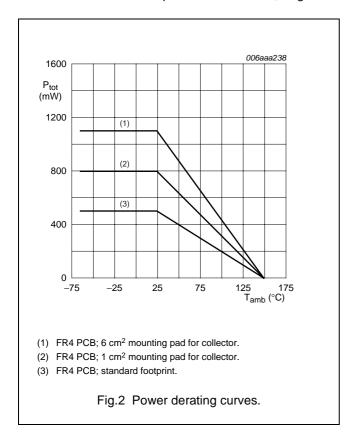
### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	60	V
$V_{CEO}$	collector-emitter voltage	open base	_	40	V
$V_{EBO}$	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		_	600	mA
I <sub>CM</sub>	peak collector current		_	800	mA
I <sub>BM</sub>	peak base current		_	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
		note 1	_	0.5	W
		note 2	_	0.8	W
		note 3	_	1.1	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

### **Notes**

- 1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
- 2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.
- 3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.



### NPN switching transistor

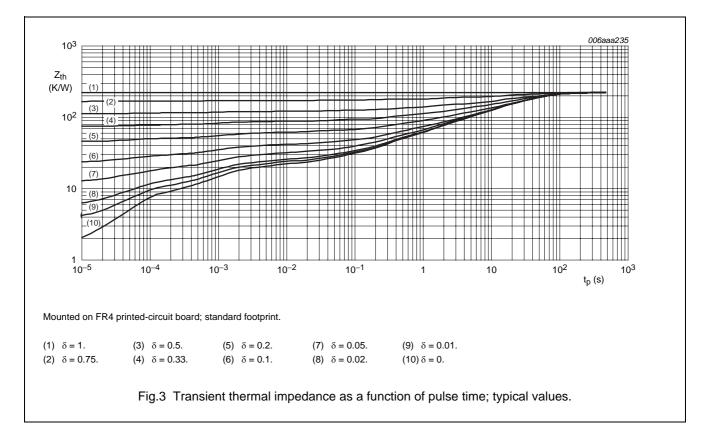
PXT4401

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to	in free air		
	ambient	note 1	250	K/W
		note 2	156	K/W
		note 3	113	K/W
R <sub>th(j-s)</sub>	thermal resistance from junction to soldering point		30	K/W

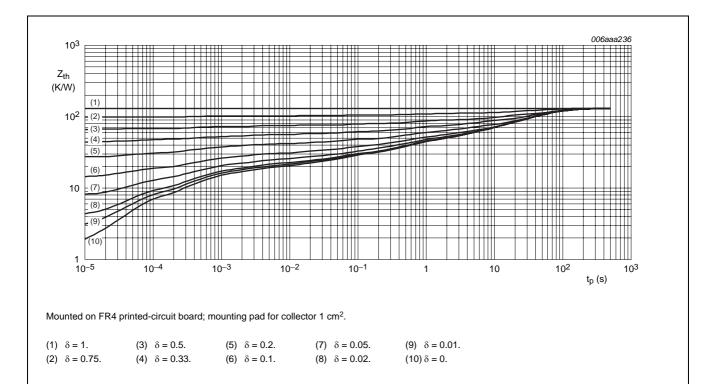
#### **Notes**

- 1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
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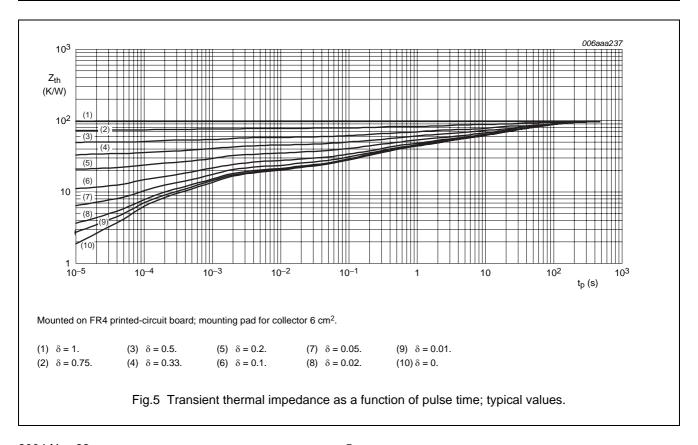


# NPN switching transistor

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 $\label{time:policy} \mbox{Fig.4 Transient thermal impedance as a function of pulse time; typical values.}$ 



# NPN switching transistor

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### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

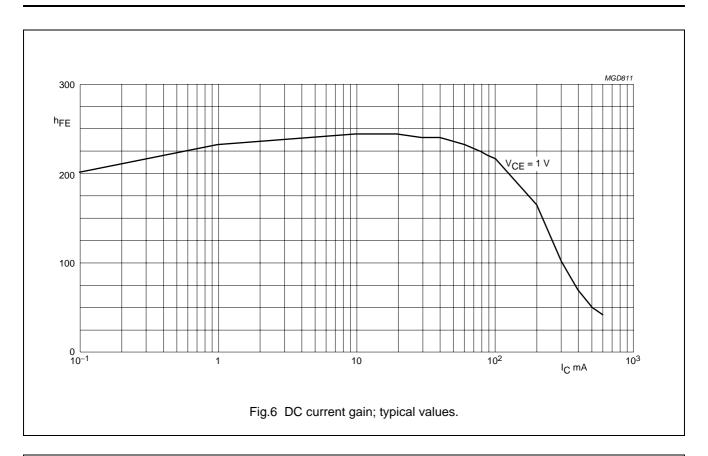
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0 A; V <sub>CB</sub> = 60 V	_	50	nA
I <sub>EBO</sub>	emitter-base cut-off current	I <sub>C</sub> = 0 A; V <sub>EB</sub> = 6 V	_	50	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V; (see Fig.6)	20	_	
		I <sub>C</sub> = 0.1 mA	20	_	
		I <sub>C</sub> = 1 mA	40	_	
		I <sub>C</sub> = 10 mA	80	_	
		I <sub>C</sub> = 150 mA; note 1	100	300	
		I <sub>C</sub> = 500 mA; V <sub>CE</sub> = 2 V; note 1	40	_	
V <sub>CEsat</sub>	collector-emitter saturation	I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA; note 1	_	400	mV
	voltage	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; note 1	_	750	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA; note 1	_	950	mV
		$I_C = 500 \text{ mA}$ ; $I_B = 50 \text{ mA}$ ; note 1	_	1.2	V
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = 5 \text{ V}; f = 1 \text{ MHz}$	_	8	pF
C <sub>e</sub>	emitter capacitance	$I_C = i_c = 0 \text{ A}; V_{EB} = 500 \text{ mV}; f = 1 \text{ MHz}$	_	30	pF
f <sub>T</sub>	transition frequency	$I_C = 20 \text{ mA}; V_{CE} = 10 \text{ V}; f = 100 \text{ MHz}$	250	_	MHz
Switching ti	imes (between 10% and 90% leve	ls); (see Fig.7)		•	
t <sub>on</sub>	turn-on time	I <sub>Con</sub> = 150 mA; I <sub>Bon</sub> = 15 mA;	_	35	ns
t <sub>d</sub>	delay time	I <sub>Boff</sub> = -15 mA	_	15	ns
t <sub>r</sub>	rise time		_	20	ns
t <sub>off</sub>	turn-off time		_	250	ns
t <sub>s</sub>	storage time		_	200	ns
t <sub>f</sub>	fall time		_	60	ns

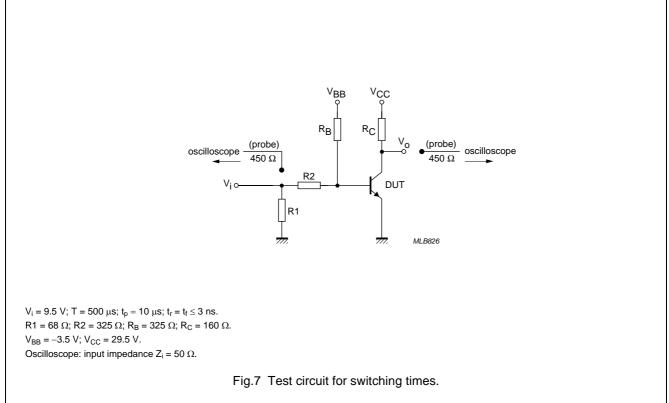
### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

# NPN switching transistor

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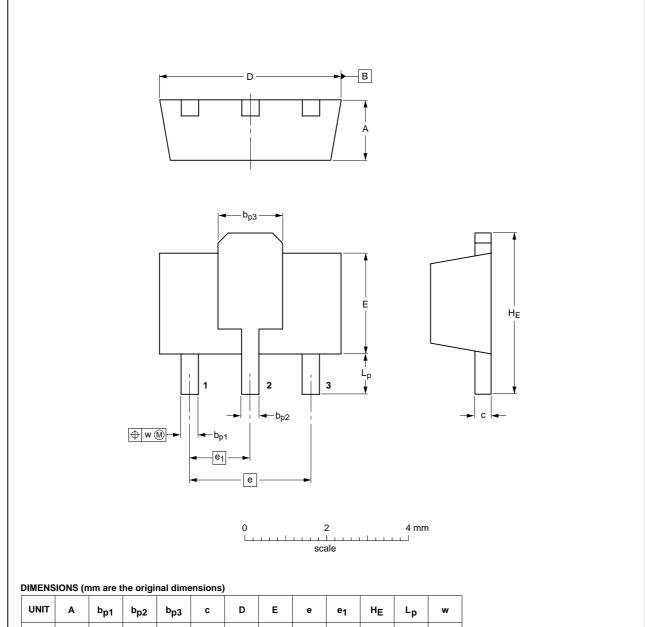
# NPN switching transistor

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### **PACKAGE OUTLINE**

### Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



UNIT	A	b <sub>p1</sub>	b <sub>p2</sub>	b <sub>p3</sub>	С	D	E	е	e <sub>1</sub>	HE	Lp
	4.0	0.40	0.50	4.0	0.44	4.0	0.0			4.05	4.0

mm 1.6 0.48 0.53 1.8 0.44 4.6 2.6 1.5 1.5 1.2 0.13 1.4 0.23 4.4 2.4 3.0 1.5 3.75 0.8 0.13	0.4	_ ^	⊌р1	□p2	ърз	"	"	_		۳1	''E	−р	**
	mm				_		l		3.0	1.5			0.13

REFERENCES				EUROPEAN	ISSUE DATE
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	TO-243	SC-62			<del>04-08-03</del> 06-03-16
	IEC	IEC JEDEC	IEC JEDEC JEITA	IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

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### NPN switching transistor

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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